

Title (en)

PROCESS FOR PRODUCING A DOUBLE LAYER WITH HETERO-JUNCTION FOR THE MEMORY ELECTRODE OF AN IMAGE REGISTRATION DEVICE

Publication

**EP 0031095 A3 19820428 (DE)**

Application

**EP 80107832 A 19801211**

Priority

DE 2951482 A 19791220

Abstract (en)

[origin: US4359488A] A double layer having a hetero-junction interface for a storage electrode of an electro-optical camera device is produced by vacuum vapor deposition of n-conductive cadmium selenide or cadmium sulfo-selenide onto a n+-conductive signal electrode layer comprised of tin oxide. The cadmium material to be vapor deposited is admixed with a small amount of a glass additive, such as boron oxide, the admixture sintered in vacuum and thereafter the cadmium material is vapor-deposited onto the signal electrode without spattering. The resultant hetero-junction is substantially free of metallic cadmium and such double layer is particularly useful in a Vidicon target.

IPC 1-7

**H01J 9/233**; **H01J 29/45**

IPC 8 full level

**H01L 31/04** (2006.01); **G03G 5/08** (2006.01); **H01J 9/233** (2006.01); **H01J 29/36** (2006.01); **H01J 29/45** (2006.01); **H01L 21/203** (2006.01); **H01L 31/18** (2006.01)

CPC (source: EP US)

**H01J 9/233** (2013.01 - EP US); **H01J 29/456** (2013.01 - EP US)

Citation (search report)

- [A] DE 1514923 A1 19700219 - TOKIO SHIBAMRA ELECTRIC CO LTD
- [A] DE 2415466 A1 19741107 - MATSUSHITA ELECTRIC IND CO LTD
- [A] DE 2527528 A1 19760108 - JAPAN BROADCASTING CORP, et al
- [A] US 2908835 A 19591013 - WEIMER PAUL K

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